

What is claimed is:

1. A semiconductor laser device comprising:
  - an active layer;
  - a lower clad layer located below said active layer;
  - 5 a first upper clad layer located above said active layer;
  - an etching stopper layer located above said first upper clad layer; and
  - a second upper clad layer located above said etching stopper layer and provided with a stripe-form protrusion, in which a stripe-form light-guiding channel is formed below said protrusion, wherein
  - said etching stopper layer is formed as a single layer and is composed of a material different from a material of each of said clad layers, and has a refractive index nearly equal to a refractive index of each of said clad layers.
- 15 2. The semiconductor laser device according to claim 1, wherein said active layer contains GaInP, each of said clad layers containing AlGaInP, and said etching stopper layer containing  $\text{Al}_x\text{Ga}_{1-x}\text{As}$  of arbitrary Al composition ratio  $x$ .
- 20 3. The semiconductor laser device according to claim 2, wherein said Al composition ratio  $x$  is larger than or equal to 0.45.
- 25 4. A semiconductor laser device comprising:

an active layer;  
a lower clad layer located below said active layer;  
a first upper clad layer located above said active layer; and

5 a second upper clad layer located above said first upper clad layer and provided with a stripe-form protrusion, in which a stripe-form light-guiding channel is formed below said protrusion, wherein

said second upper clad layer is composed of a material  
10 different from a material of said first upper clad layer, and has a refractive index nearly equal to a refractive index of said first upper clad layer.

5. The semiconductor laser device according to claim 4, wherein said active layer contains GaInP, each of said  
15 lower clad layer and said first upper clad layer containing AlGaInP, and said second upper clad layer containing  $\text{Al}_x\text{Ga}_{1-x}\text{As}$  of arbitrary Al composition ratio  $x$ .

6. The semiconductor laser device according to claim 5, wherein said Al composition ratio  $x$  is larger than or equal  
20 to 0.45.